Complementary Silicon Power Plastic Transistors

These devices are designed for low power audio amplifier and low-current, high-speed switching applications.

Features

- High Collector-Emitter Sustaining Voltage
- High DC Current Gain
- Low Collector-Emitter Saturation Voltage
- High Current Gain Bandwidth Product
- Annular Construction for Low Leakages
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	100	Vdc
Collector-Base Voltage	V _{CB}	100	Vdc
Emitter-Base Voltage	V _{EB}	7.0	Vdc
Collector Current – Continuous	Ic	4.0	Adc
Collector Current – Peak	I _{CM}	8.0	Adc
Base Current	I _B	10	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	15 120	W mW/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

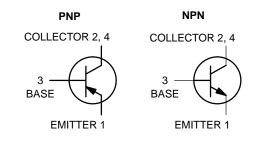
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	8.34	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	83.4	°C/W



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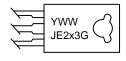
http://onsemi.com

4.0 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 100 VOLTS, 15 WATTS





MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping
MJE243G	TO-225 (Pb-Free)	500 Units/Box
MJE253G	TO-225 (Pb-Free)	500 Units/Box

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	-		•	-
Collector–Emitter Sustaining Voltage ($I_C = 10 \text{ mAdc}, I_B = 0$)	V _{CEO(sus)}	100	-	V
Collector Cutoff Current $(V_{CB} = 100 \text{ Vdc}, I_E = 0)$ $(V_{CE} = 100 \text{ Vdc}, I_E = 0, T_C = 125^{\circ}\text{C})$	Ісво	- -	0.1 0.1	μA mA
Emitter Cutoff Current $(V_{BE} = 7.0 \text{ Vdc}, I_{C} = 0)$	I _{EBO}	-	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 200 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 1.0 \text{ Vdc}$)	h _{FE}	40 15	180 -	_
Collector–Emitter Saturation Voltage ($I_C = 500$ mAdc, $I_B = 50$ mAdc) ($I_C = 1.0$ Adc, $I_B = 100$ mAdc)	V _{CE(sat)}	- -	0.3 0.6	V
Base–Emitter Saturation Voltage ($I_C = 2.0$ Adc, $I_B = 200$ mAdc)	V _{BE(sat)}	-	1.8	V
Base–Emitter On Voltage (I _C = 500 mAdc, V _{CE} = 1.0 Vdc)	V _{BE(on)}	-	1.5	V
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product $(I_C = 100 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f_{test} = 10 \text{ MHz})$	f _T	40	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz)	C _{ob}	-	50	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

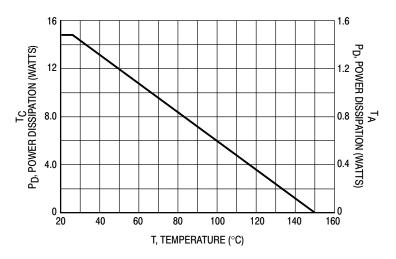


Figure 1. Power Derating

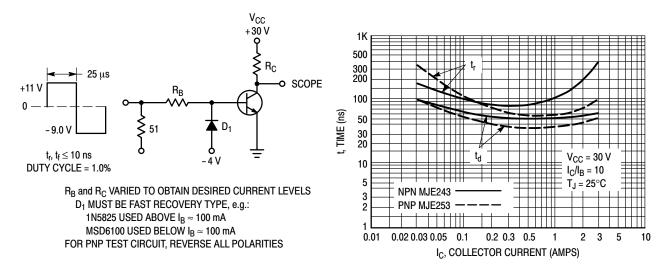


Figure 2. Switching Time Test Circuit

Figure 3. Turn-On Time

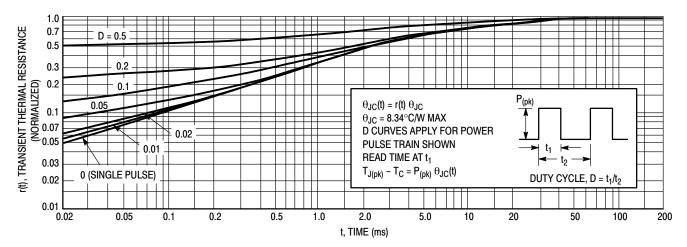


Figure 4. Thermal Response

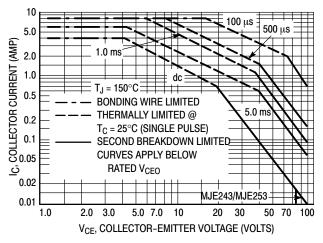


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

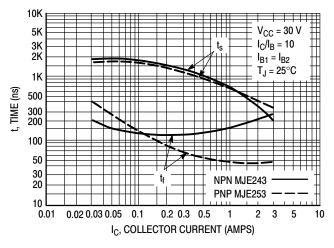


Figure 6. Turn-Off Time

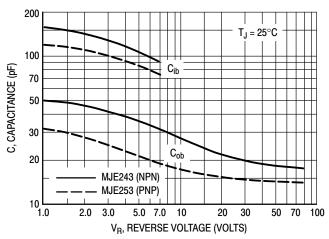


Figure 7. Capacitance

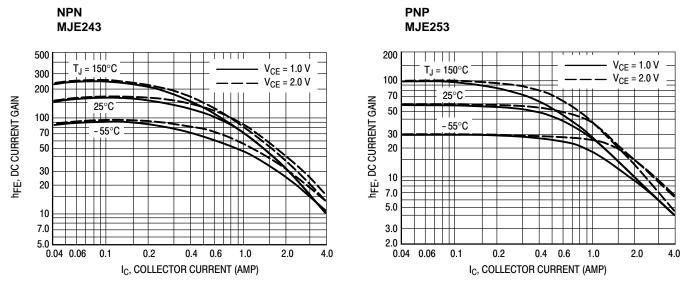


Figure 8. DC Current Gain

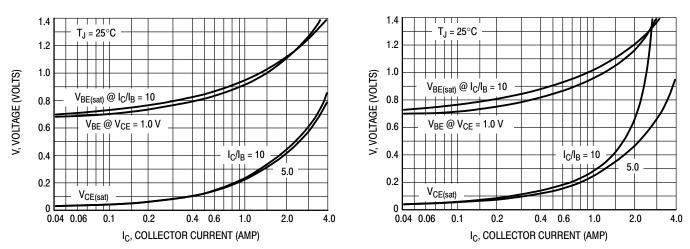


Figure 9. "On" Voltages

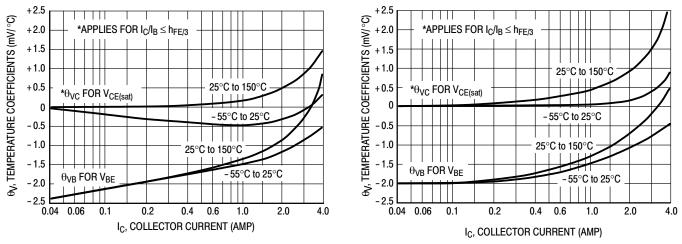
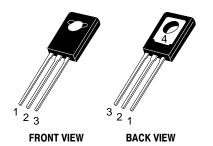
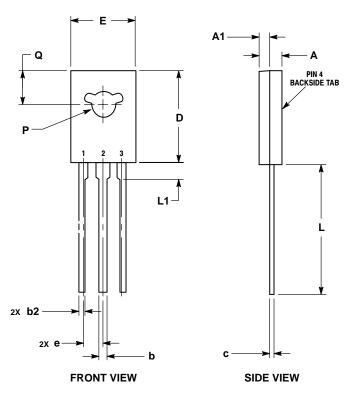


Figure 10. Temperature Coefficients

PACKAGE DIMENSIONS



TO-225 CASE 77-09 **ISSUE AC**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.40	3.00	
A1	1.00	1.50	
b	0.60	0.90	
b2	0.51	0.88	
С	0.39	0.63	
D	10.60	11.10	
E	7.40	7.80	
е	2.04	2.54	
L	14.50	16.63	
L1	1.27	2.54	
P	2.90	3.30	
Q	3.80	4.20	

STYLE 1:

PIN 1. EMITTER 2., 4. COLLECTOR 3. BASE

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